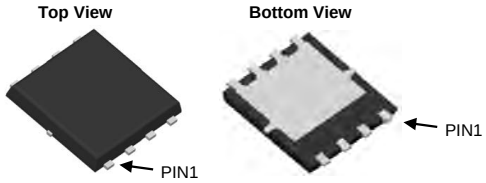
N-Channel 150 V (D-S) MOSFET

PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (mΩ)(Typ.)	I_D (A)[a]	Q_g (Typ.)
150	15 at V_{GS} = 10 V	70	38 nC

DFN5X6



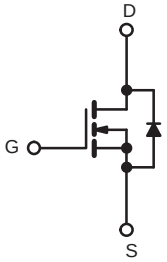
FEATURES

- DT-Trench Power MOSFET
- 100 % Rg and UIS Tested

RoHS COMPLIANT

APPLICATIONS

- Synchronous rectification
- Primary side switch
- DC/DC converters
- OR-ing
- Power supplies
- Motor drive control
- Battery and load switch



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)				
Parameter		**Symbol**	**Limit**	**Unit**
Drain-Source Voltage		V_{DS}	150	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current (T_J = 150 °C)	T_C = 25 °C	I_D	70	A
	T_C = 70 °C		60.5	
Pulsed Drain Current		I_{DM}	280	
Single-Pulse Avalanche Energy		E_{AS}	150	mJ
Maximum Power Dissipation	T_C = 25 °C	P_D	189	W
	T_C = 70 °C		121	
	T_A = 25 °C		8.9[b,c]	
	T_A = 70 °C		5.71[b,c]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS					
Parameter		**Symbol**	**Typical**	**Maximum**	**Unit**
Maximum Junction-to-Ambient [b]	t ≤ 10 s	R_{thJA}	10	14	°C/W
Maximum Junction-to-Case	Steady State	R_{thJC}	0.5	0.66	

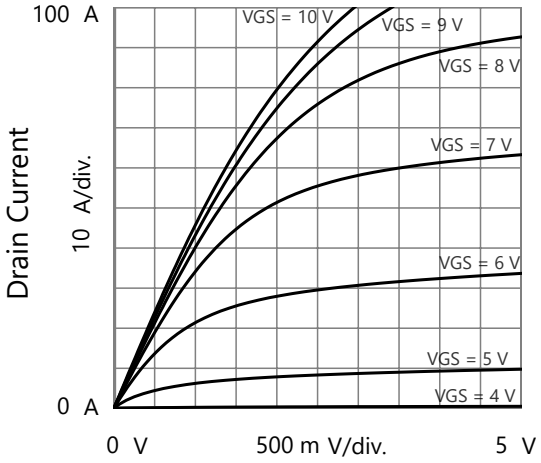
Notes:
a. Based on T_C = 25 °C.
b. Surface mounted on 1" x 1" FR4 board.
c. t = 10 s.

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0, I_D = 250 µA	150			V
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	2		4	V
Gate-Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 100V, V_{GS} = 0 V			1	µA
		V_{DS} = 100V, V_{GS} = 0 V, T_J = 55 °C			10	
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} ≥ 5 V, V_{GS} = 10 V	70			A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 20 A		15	18.5	mΩ
Forward Transconductance[a]	g_{fs}	V_{DS} = 10 V,I_D = 20 A		11		S
Dynamic[b]						
Input Capacitance	C_{iss}	V_{DS} = 50 V, V_{GS} = 0 V, f = 1 MHz		2490		pF
Output Capacitance	C_{oss}			230		
Reverse Transfer Capacitance	C_{rss}			3		
Total Gate Charge	Q_g	V_{DS} = 50 V, V_{GS} = 10 V, I_D = 20 A		38		nC
Gate-Source Charge	Q_{gs}			9		
Gate-Drain Charge	Q_{gd}			8.8		
Gate Resistance	R_g	f = 1 MHz		1.2		Ω
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 50 V, R_L = 2.5 Ω I_D ≅ 20 A, V_{GEN} = 10 V, R_g = 1 Ω		15		ns
Rise Time	t_r			23		
Turn-Off DelayTime	$t_{d(off)}$			47		
Fall Time	t_f			12		
Drain-Source Body Diode Characteristics						
Continous Source-Drain Diode Current	I_S	T_C = 25 °C			70	A
Pulse Diode Forward Current (100 µs)	I_{SM}				280	
Body Diode Voltage	V_{SD}	I_S = 1 A			1.2	V
Body Diode Reverse Recovery Time	t_{rr}	I_F = 20 A, dI/dt = 100 A/µs, T_J = 25 °C		50		ns
Body Diode Reverse Recovery Charge	Q_{rr}			71		nC
Reverse recovery fall time	t_a			26		ns
Reverse recovery rise time	t_b			21		

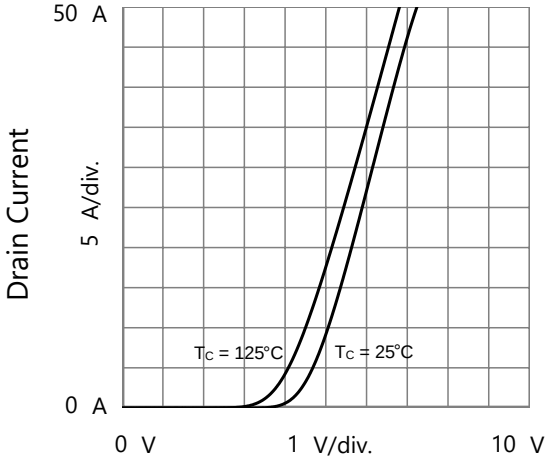
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

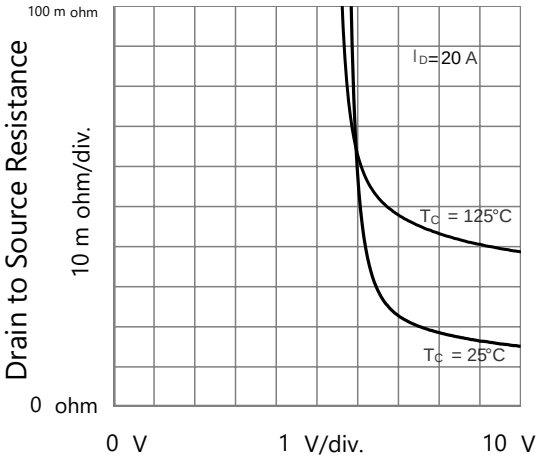
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



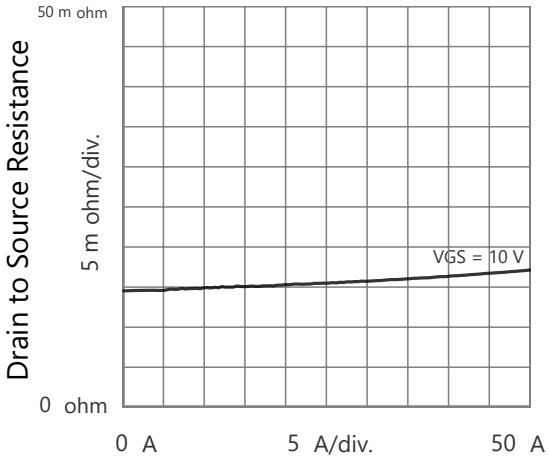
Drain to Source Voltage
Output Characteristics



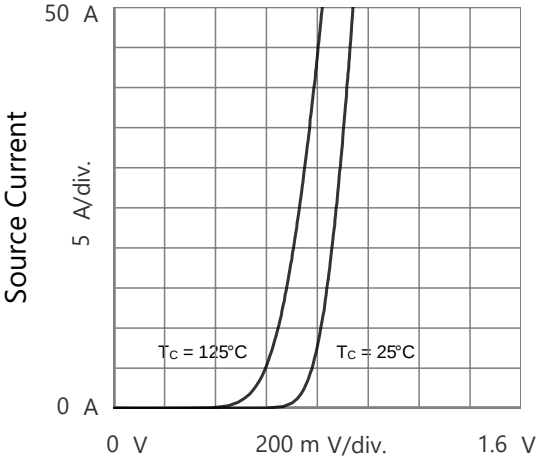
Gate to Source Voltage
Transfer Characteristics



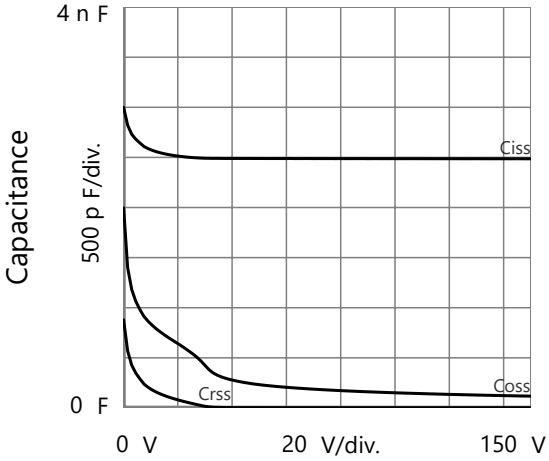
Gate to Source Voltage
Drain to Source Resistance vs. Gate to Source Voltage



Drain Current
Drain to Source Resistance vs. Drain Current

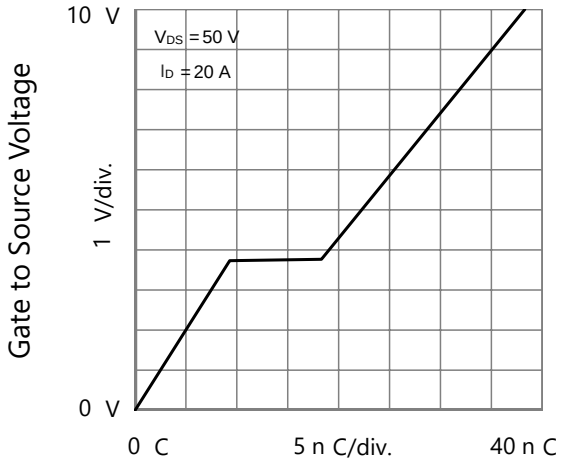


Source to Drain Voltage
Body Diode Forward Characteristics

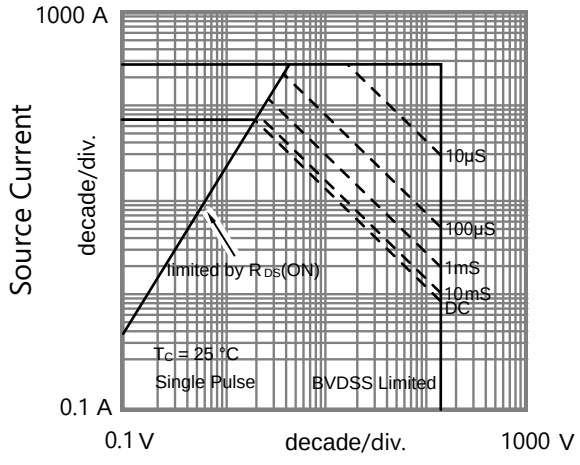


Drain to Source Voltage
Capacitances

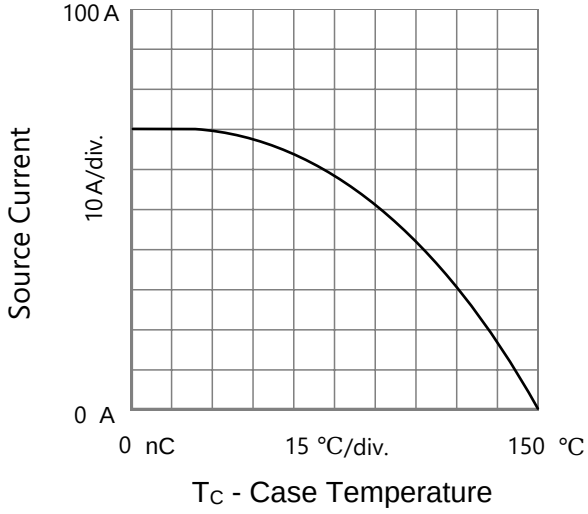
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

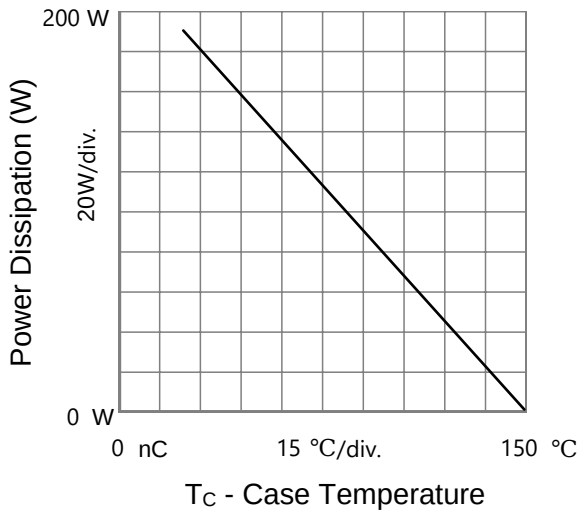


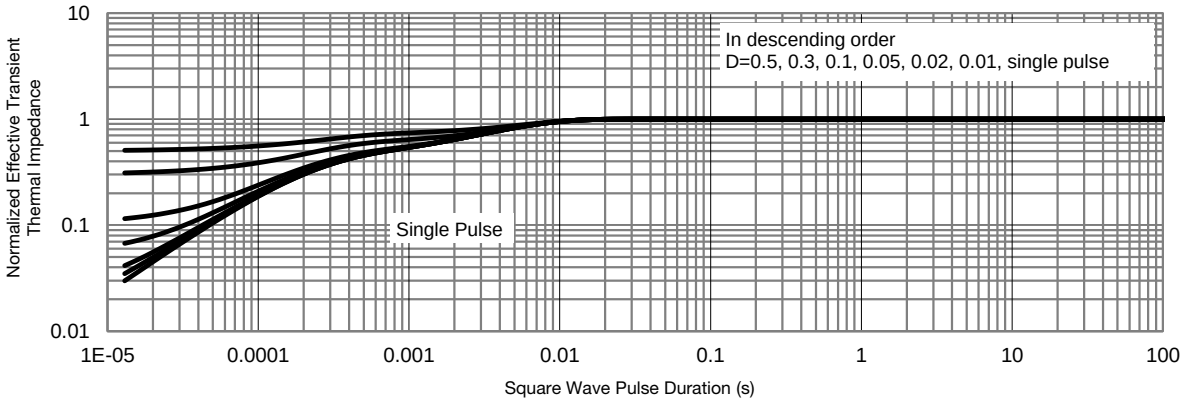
Gate to Source Voltage vs. GateCharge



Safe Operating Area, Junction-to-Ambient







Normalized Thermal Transient Impedance, Junction-to-Case

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